L	Hits	Search Text	DB	Time stamp
Number				
3	395	moisture and alcohol and gate and source and drain	USPAT; US-PGPUB; EPO; JPO;	2004/06/24 19:05
4	129	moisture and alcohol and gate and source and drain and metal adj oxide and heat\$4	DERWENT USPAT; US-PGPUB; EPO; JPO;	2004/06/24 19:07
5	0	moisture adj sensor and alcohol adj sensor and gate and source and drain and metal adj oxide and heat\$4	DERWENT USPAT; US-PGPUB; EPO; JPO;	2004/06/24 19:07
6	0	moisture adj sensor and alcohol adj sensor and gate and source and drain	DERWENT USPAT; US-PGPUB; EPO; JPO;	2004/06/24 19:07
7	23	moisture same alcohol and gate and source and drain	DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/24 19:08
8	6	moisture same alcohol same (detect\$4 or sens\$4 or determin\$4 or assay or test\$4 or meausur\$4 or monitor\$4) and gate and source and drain	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/24 19:09
-	3	"10110471"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/17 15:45
	1	fleisher and meixner	USPAT; US-PGPUB; EPO; JPO;	2004/06/17 16:09
_	12	gas adj sensitive adj field adj effect adj transistor	DERWENT USPAT; US-PGPUB; EPO; JPO;	2004/06/17 16:28
-	102542	field adj effect adj transistor	DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/17 16:28
-	1704	gas same field adj effect adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/17 16:28
-	969	gas same field adj effect adj transistor and drain and source and gate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/17 16:29
	1	gas same field adj effect adj transistor and drain and source and gate and polycyclopentylsilsesquioxane	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/17
-	5 }	gas same field adj effect adj transistor and drain and source and gate and silsesquioxane	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/17
-	1	gas same field adj effect adj transistor and drain and source and gate and polysilsesquioxane	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/17 16:35
-	16	drain and source and gate and polysilsesquioxane	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/17 16:35
-	4	gas same field adj effect adj transistor and drain and source and gate and scandium adj oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/17 16:36

-	189	drain and source and gate and scandium	USPAT;	2004/06/17
		adj oxide	US-PGPUB;	16:36
			EPO; JPO;	10.30
ľ			DERWENT	1
-	16	drain and source and gate and scandium	USPAT;	2004/06/17
		adj oxide and alcohol	US-PGPUB:	16:37
			EPO; JPO;	
	İ		DERWENT	
-	37	drain and source and gate and scandium	USPAT;	2004/06/17
		adj oxide and gas	US-PGPUB;	16:53
			EPO; JPO;	
i			DERWENT	
-	195997	drain and source and gate	USPAT;	2004/06/17
			US-PGPUB;	16:39
			EPO; JPO;	
			DERWENT	
-	86	drain and source and gate and gas and	USPAT;	2004/06/17
		substrate and polysiloxane	US-PGPUB;	16:54
			EPO; JPO;	
			DERWENT	
_	48	drain and source and gate and gas and	USPAT;	2004/06/17
		substrate and polysiloxane and alcohol	US-PGPUB;	17:20
			EPO; JPO;	
			DERWENT	
_	2093	drain and source and gate and gas and	USPAT;	2004/06/17
		substrate and moisture	US-PGPUB;	17:21
			EPO; JPO;	
	1 !		DERWENT	
_	17	drain and source and gate and gas and	USPAT;	2004/06/17
		substrate and moisture adj sensitive	US-PGPUB;	17:21
			EPO; JPO;]
L			DERWENT	